

# DATA SHEET

## **PDTA123E series**

PNP resistor-equipped transistors;

$R1 = 2.2\text{ k}\Omega$ ,  $R2 = 2.2\text{ k}\Omega$

Product specification  
Supersedes data of 1999 May 21

2003 Apr 14

## PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTA123E series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	–50	V
I <sub>O</sub>	output current (DC)	–	–100	mA
R1	bias resistor	2.2	–	k $\Omega$
R2	bias resistor	2.2	–	k $\Omega$

### DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA123EK	SOT346	SC-59	42	PDTC123EK
PDTA123EM	SOT883	SC-101	DH	PDTC123EM
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES
PDTA123ET	SOT23	–	*21 <sup>(1)</sup>	PDTC123ET
PDTA123EU	SOT323	SC-70	*42 <sup>(1)</sup>	PDTC123EU

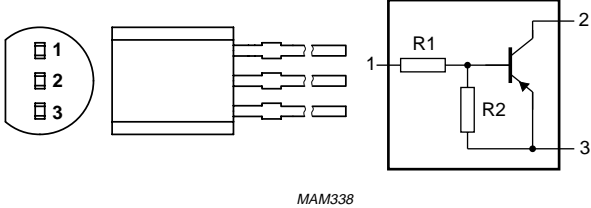
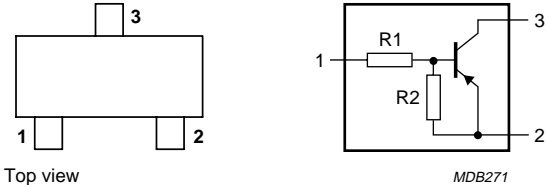
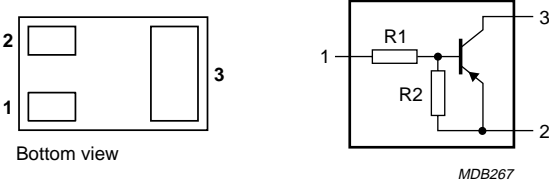
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA123ES		1 2 3	base collector emitter
PDTA123EK PDTA123ET PDTA123EU		1 2 3	base emitter collector
PDTA123EM		1 2 3	base emitter collector

# PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTA123E series

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–10	V
V <sub>I</sub>	input voltage				
	positive		–	+10	V
	negative		–	–12	V
I <sub>O</sub>	output current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT883	notes 2 and 3	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT883	notes 2 and 3	500	K/W

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

PNP resistor-equipped transistors;  
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**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0	–	–	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0	–	–	-1	$\mu$ A
		V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	-50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0	–	–	-2	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -20 mA	30	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA	–	–	-150	mV
V <sub>i(off)</sub>	input-off voltage	I <sub>C</sub> = -1 mA; V <sub>CE</sub> = -5 V	–	-1.2	-0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = -20 mA; V <sub>CE</sub> = -0.3 V	-2	-1.6	–	V
R1	input resistor		1.54	2.2	2.86	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = -10 V; f = 1 MHz	–	–	3	pF

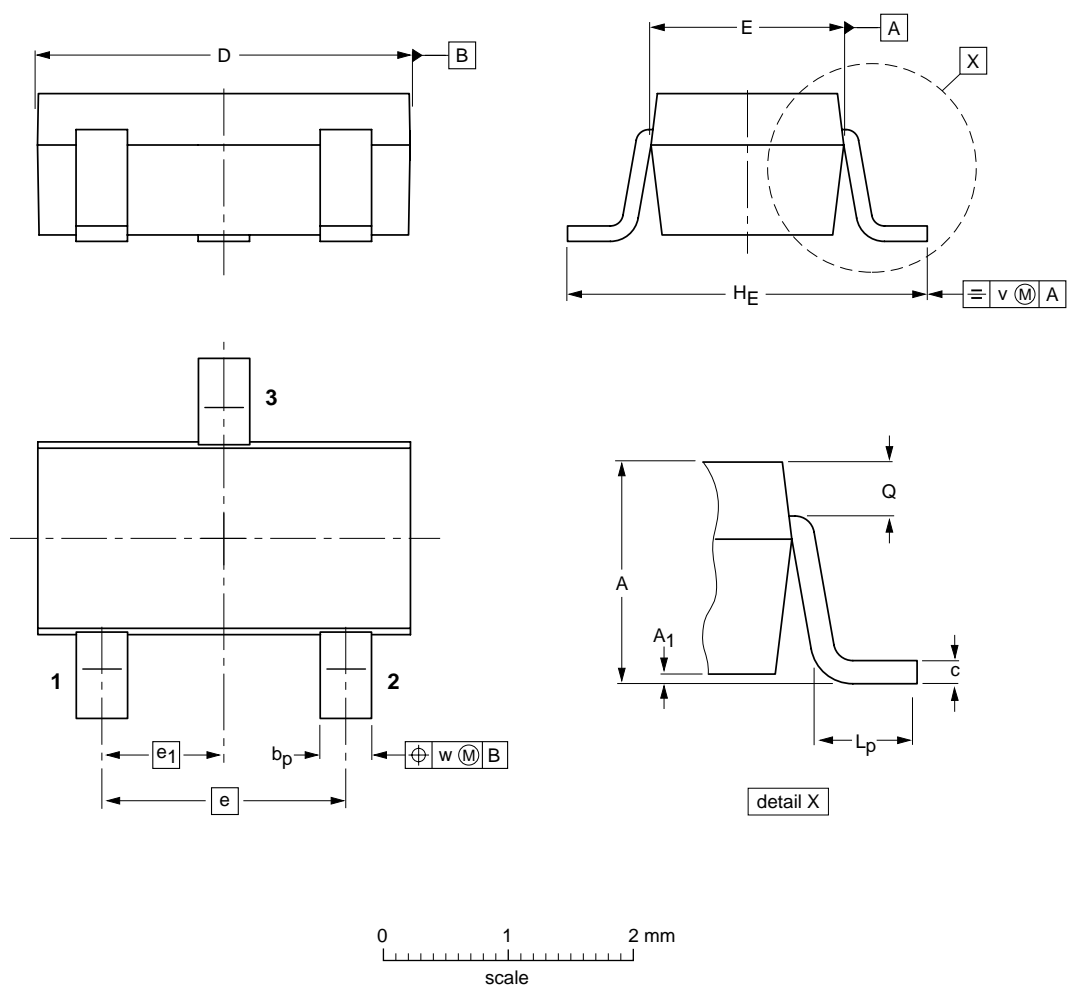
PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

PACKAGE OUTLINES


Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

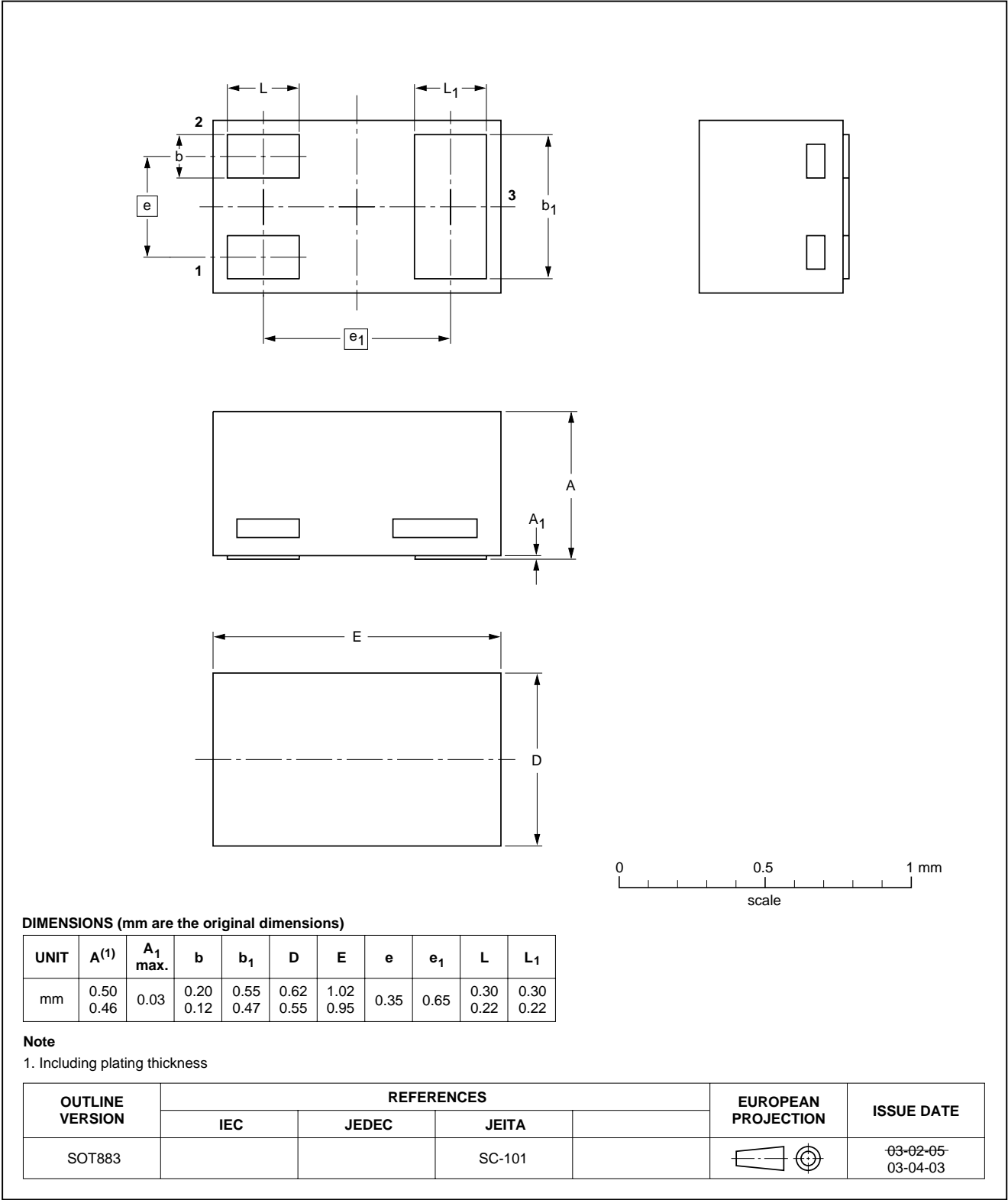
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

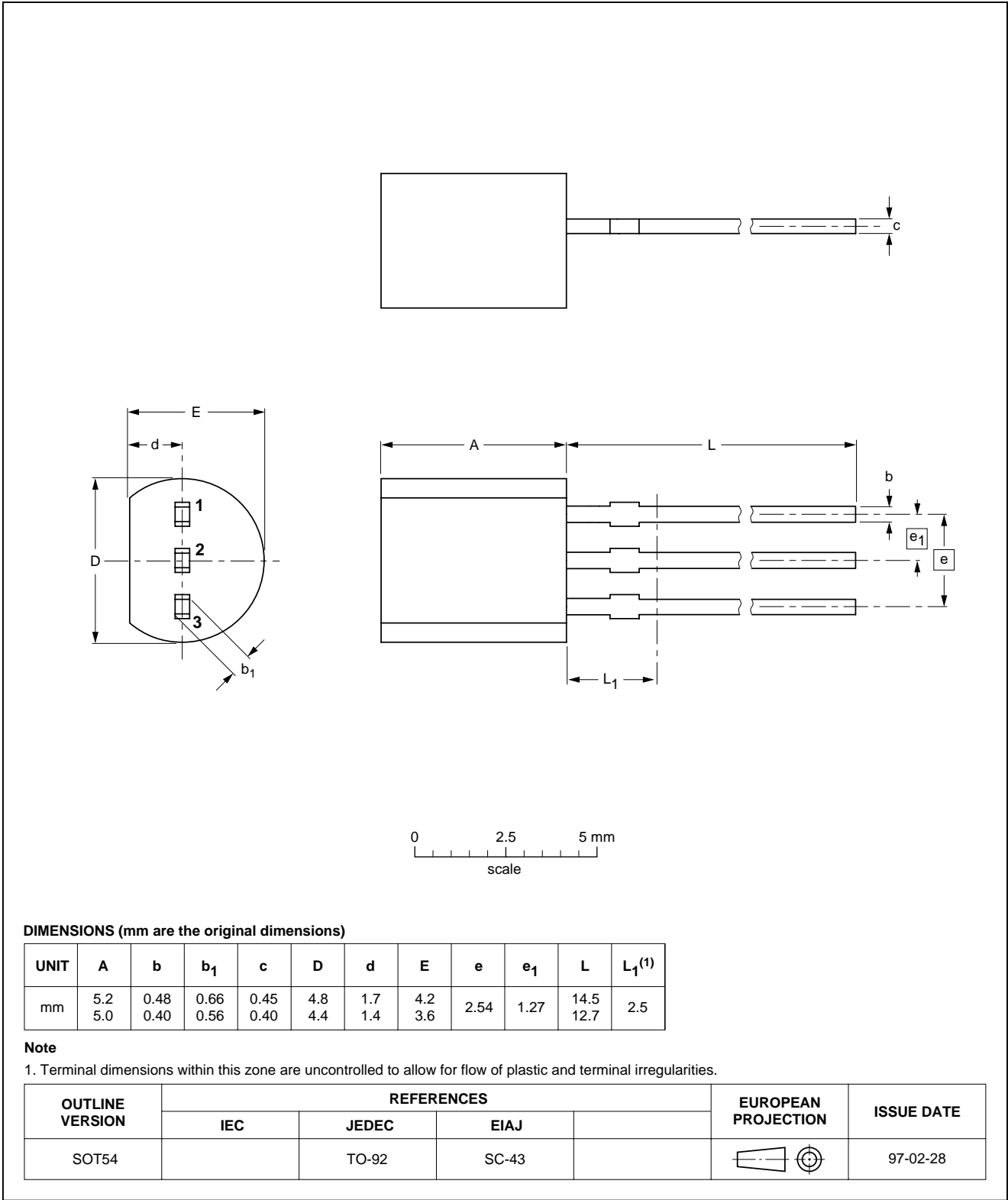


PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

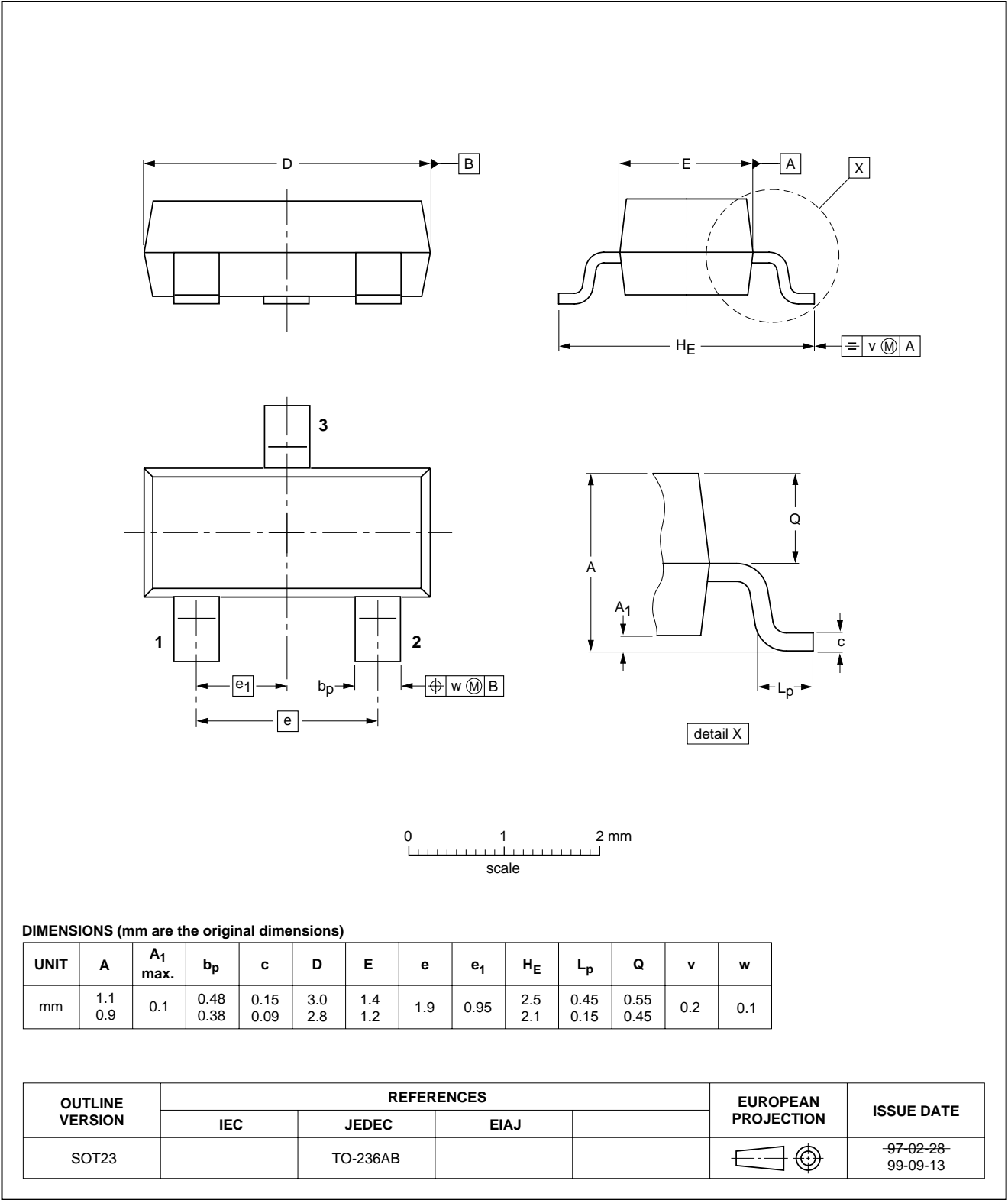


PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface mounted package; 3 leads

SOT23

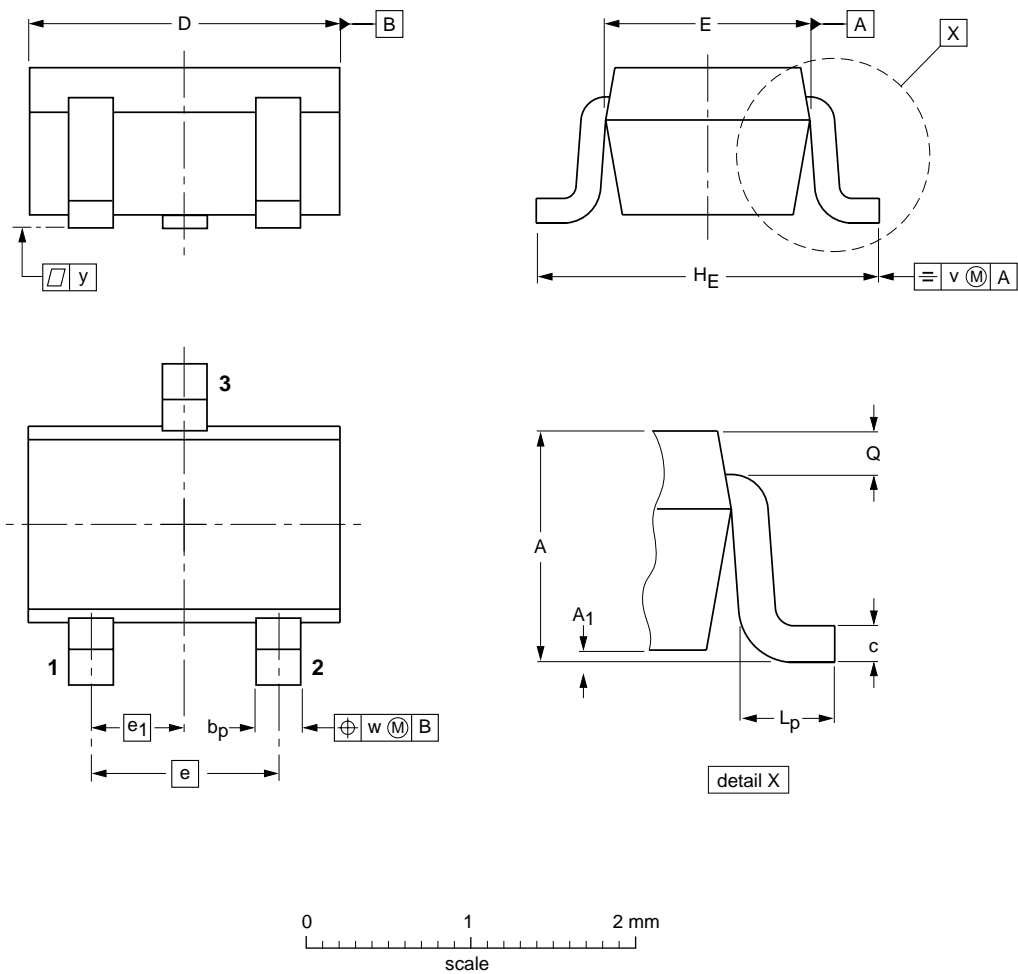


PNP resistor-equipped transistors;  
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP resistor-equipped transistors;  
R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

PDTA123E series

#### DATA SHEET STATUS

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I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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